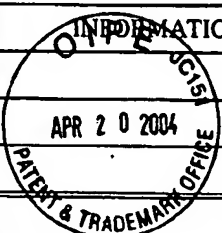
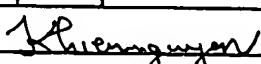


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				M-15230 US		10/632,154		
 INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				Applicant				
				Yi Ding				
				Filing Date		Group		
				July 30, 2003		Unassigned 2823		
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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
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							Translation	
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	AJ							
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Examiner								
		Date Considered 07/23/04						
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Examiner <i>KP</i>	Date Considered <i>07/23/04</i>
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		July 30, 2003	Unassigned 2823
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KN	AZ	United States Patent Application No. 10/631,941, entitled "Nonvolatile Memory Cell With Multiple Floating Gates Formed After The Select Gate," Filed on July 30, 2003; Attorney Docket No.: M-15171 US.	
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	BG		
	BH		
Examiner <i>Phienagyal</i>		Date Considered <i>07/23/04</i>	
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				Filed Herewith		Unassigned 2823	
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Applicant(s)	
(Use several sheets if necessary)	Yi Ding	
	Filing Date 07/30/03	Group
	Filed Herewith	Unassigned 2828

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Y	BH	
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Examiner

Khien Nguyen

Date Considered

07/23/04

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